

MMBT5401LT1 TRANSISTOR (PNP)

FEATURES

Power dissipation

$$P_{CM}: 0.3 \text{ W (Tamb=25°C)}$$

Collector current

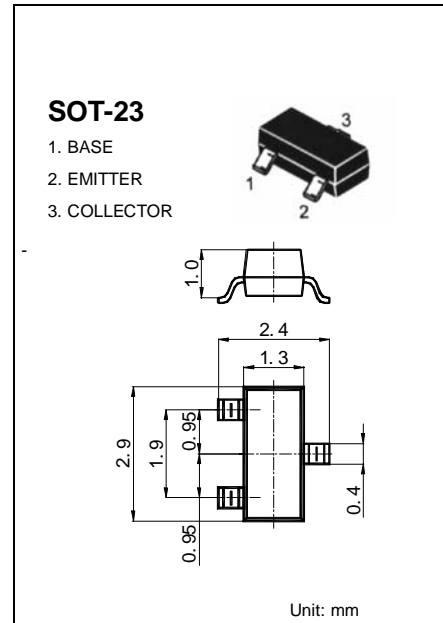
$$I_{CM}: -0.6 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO}: -160 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55°C \text{ to } +150°C$$



ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100 \mu A, I_E = 0$	-160		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1 \text{ mA}, I_B = 0$	-150		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10 \mu A, I_C = 0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB} = -120V, I_E = 0$		-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -4V, I_C = 0$		-0.1	μA
DC current gain	$H_{FE(1)}$	$V_{CE} = -5V, I_C = -1mA$	80		
	$H_{FE(2)}$	$V_{CE} = -5V, I_C = -10mA$	100	200	
	$H_{FE(3)}$	$V_{CE} = -5V, I_C = -50mA$	50		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -50mA, I_B = -5mA$		-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -50mA, I_B = -5mA$		-1	V
Transition frequency	f_T	$V_{CE} = -5V, I_C = -10mA$ $f = 30MHz$	100		MHz

DEVICE MARKING

MMBT5401LT1=2L